

N-channel 30 V 11.6 m $\Omega$  logic level MOSFET in LFPAK using NextPower technology

Rev. 3 — 24 October 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

### **1.3 Applications**

Quick reference data

Table 1.

- DC-to-DC converters
- Load switching

### Synchronous buck regulator

### 1.4 Quick reference data

	Guick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	37	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	29	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 10 \text{ A}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \\ \text{see } \overline{\text{Figure 12}} \end{array}$	-	12.3	14.5	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; see <u>Figure 12</u>	-	9.9	11.6	mΩ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 10 A; V <sub>DS</sub> = 15 V; see Figure 14; see Figure 15	-	1.4	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS}$ = 4.5 V; $I_D$ = 10 A; $V_{DS}$ = 15 V; see Figure 14; see Figure 15	-	4.9	-	nC

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### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		2
2	S	source	mb	
3	S	source		
4	G	gate	Q;	
mb	D	mounting base; connected to drain	$\begin{array}{c} \hline \\ \hline \\ 1 \\ 2 \\ 3 \\ 4 \\ \end{array}$	mbb076 S

#### SOT669 (LFPAK; Power-SO8)

### 3. Ordering information

Table 3. Orderin	information		
Type number	Package		
	Name	Description	Version
PSMN011-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

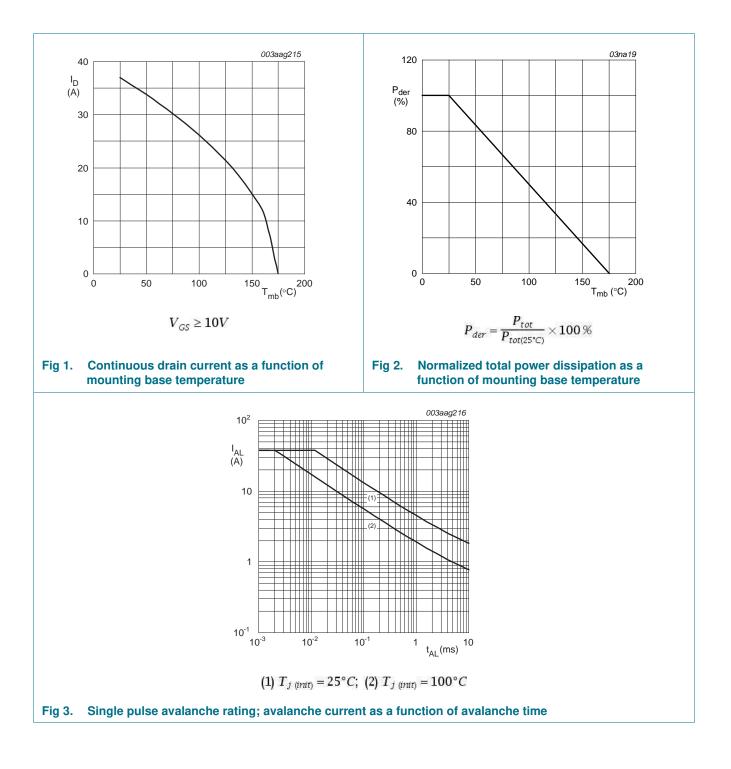
### 4. Limiting values

#### Table 4.Limiting values

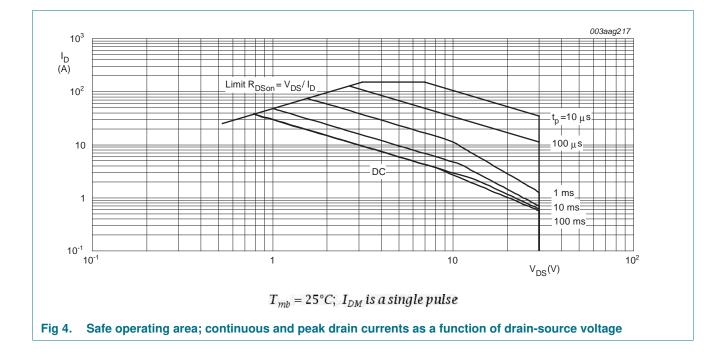
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	25 °C $\leq$ T <sub>j</sub> $\leq$ 175 °C; R <sub>GS</sub> = 20 k $\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	37	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	26	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <u>Figure 4</u>	-	150	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	29	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	140	-	V
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	26	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	150	А
Avalanche r	uggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(\text{init})} = 25 \ ^{\circ}\text{C}; \ I_{D} = 37 \text{ A}; \\ V_{sup} \leq 30 \text{ V}; \ R_{GS} = 50 \ \Omega; \ unclamped; \\ see \ \underline{Figure \ 3} \end{array} $	-	9	mJ

# PSMN011-30YLC



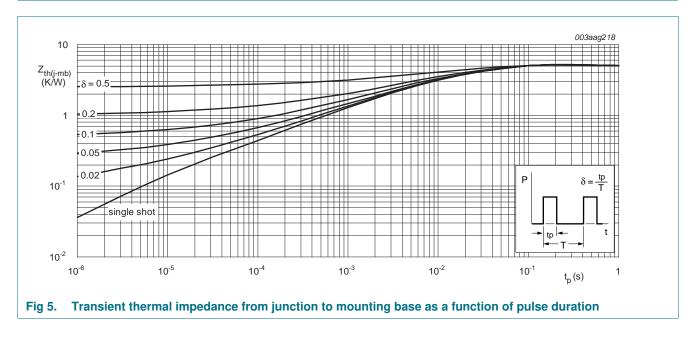
# PSMN011-30YLC



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### 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 5	-	4.87	5.06	K/W



### N-channel 30 V 11.6 mΩ logic level MOSFET in LFPAK using NextPower technology

### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.57	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	12.3	14.5	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 10 A; $T_j$ = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	23.4	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; see <u>Figure 12</u>	-	9.9	11.6	mΩ
	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	18.8	mΩ	
R <sub>G</sub>	gate resistance	f = 1 MHz	-	2	4	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	10.3	-	nC
		<u></u>				
		$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15	-	4.9	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	4.9 9	-	nC nC
Q <sub>GS</sub>	gate-source charge	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ \text{see Figure 14}; \text{see Figure 15} \\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \end{split}$	-			
	gate-source charge pre-threshold gate-source charge	$I_{D} = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15 $I_{D} = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$		9	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ \text{see Figure 14}; \text{see Figure 15} \\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \end{split}$	-	9 1.5	-	nC nC
Q <sub>GS(th)</sub> Q <sub>GS(th-pl)</sub>	pre-threshold gate-source charge post-threshold gate-source	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ \text{see Figure 14}; \text{see Figure 15} \\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \end{split}$	-	9 1.5 1.1	-	nC nC nC
Q <sub>GS(th)</sub> Q <sub>GS(th-pl)</sub> Q <sub>GD</sub>	pre-threshold gate-source charge post-threshold gate-source charge	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ \text{see Figure 14}; \text{see Figure 15} \\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \end{split}$	-	9 1.5 1.1 0.4	-	nC nC nC nC
$Q_{GS(th)}$ $Q_{GS(th-pl)}$ $Q_{GD}$ $V_{GS(pl)}$	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ \text{see Figure 14}; \text{ see Figure 15}\\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}\\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ \text{see Figure 14}; \text{ see Figure 15}\\ \end{split}$	-	9 1.5 1.1 0.4 1.4	-	nC nC nC nC
Q <sub>GS</sub> (th) Q <sub>GS</sub> (th-pl) Q <sub>GD</sub> V <sub>GS</sub> (pl) C <sub>iss</sub>	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage	$\begin{split} & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ & \text{see Figure 14}; \text{ see Figure 15} \\ & I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ & \text{see Figure 14}; \text{ see Figure 15} \\ \end{split}$	- - -	9 1.5 1.1 0.4 1.4 2.5		nC nC nC nC v
Q <sub>GS</sub> (th) Q <sub>GS</sub> (th-pl) Q <sub>GD</sub> V <sub>GS</sub> (pl) C <sub>iss</sub> C <sub>oss</sub>	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance	$I_{D} = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15 $I_{D} = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ $I_{D} = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15 $I_{D} = 10 \text{ A}; V_{DS} = 15 \text{ V}; \text{see Figure 14};$ see Figure 15 $V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	- - - -	9 1.5 1.1 0.4 1.4 2.5 641	- - - -	nC nC nC nC V
Q <sub>GS</sub> (th) Q <sub>GS</sub> (th-pl) Q <sub>GD</sub> V <sub>GS</sub> (pl) C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance	$\begin{split} &I_{D} = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ &\text{see Figure 14}; \text{ see Figure 15}\\ &I_{D} = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}\\ &I_{D} = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ &\text{see Figure 14}; \text{ see Figure 15}\\ \end{split}$	- - - - - - -	9 1.5 1.1 0.4 1.4 2.5 641 146	- - - - - -	nC nC nC nC V V
Q <sub>GS</sub> (th) Q <sub>GS</sub> (th-pl) Q <sub>GD</sub> V <sub>GS</sub> (pl) C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance	$\begin{split} & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ & \text{see Figure 14}; \text{ see Figure 15} \\ & I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ & \text{see Figure 14}; \text{ see Figure 15} \\ & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ see Figure 15} \\ & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ see Figure 14}; \\ & \text{see Figure 15} \\ & V_{DS} = 15 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz}; \\ & \text{T}_j = 25 \text{ °C}; \text{ see Figure 16} \end{split}$	- - - - - - - - -	9 1.5 1.1 0.4 1.4 2.5 641 146 46	- - - - -	nC nC nC nC V pF pF
Q <sub>GS</sub> Q <sub>GS</sub> (th) Q <sub>GS</sub> (th-pl) Q <sub>GD</sub> V <sub>GS</sub> (pl) C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> t <sub>d</sub> (on) t <sub>r</sub> t <sub>d</sub> (off)	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance turn-on delay time	$\begin{split} &I_{D} = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ &\text{see Figure 14}; \text{ see Figure 15}\\ &I_{D} = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}\\ &I_{D} = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ &\text{see Figure 14}; \text{ see Figure 15}\\ \end{split}$	- - - - - - - - - -	9 1.5 1.1 0.4 1.4 2.5 641 146 46 13.4	- - - - - - - -	nC nC nC nC V V pF pF pF

PSMN011-30YLC
Product data sheet

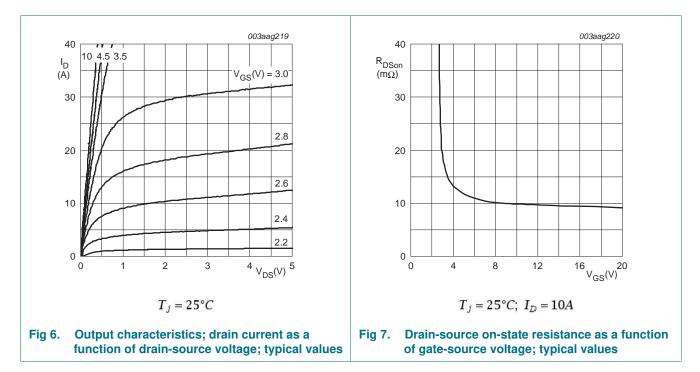
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# PSMN011-30YLC

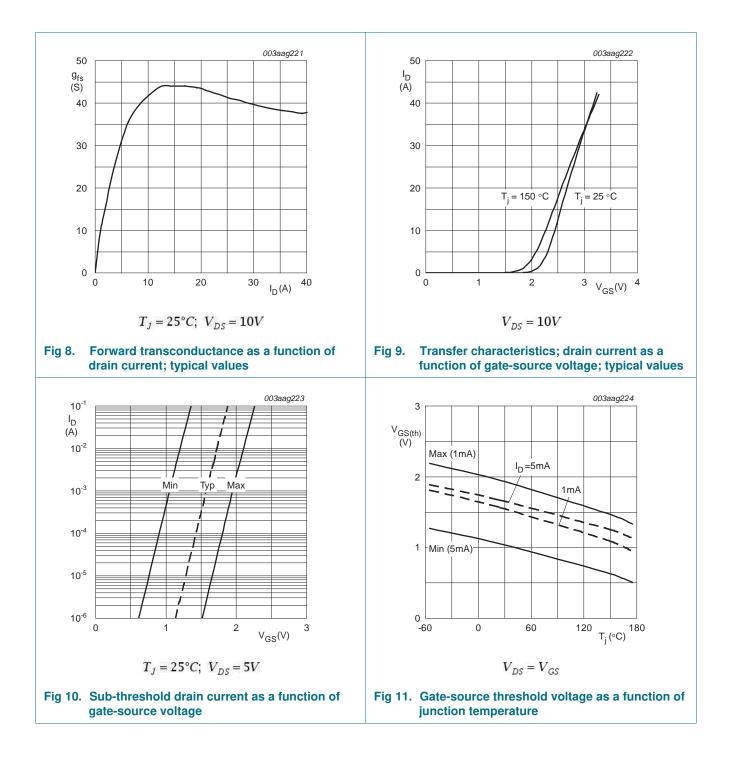
#### N-channel 30 V 11.6 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

#### Table 6. Characteristics ...continued

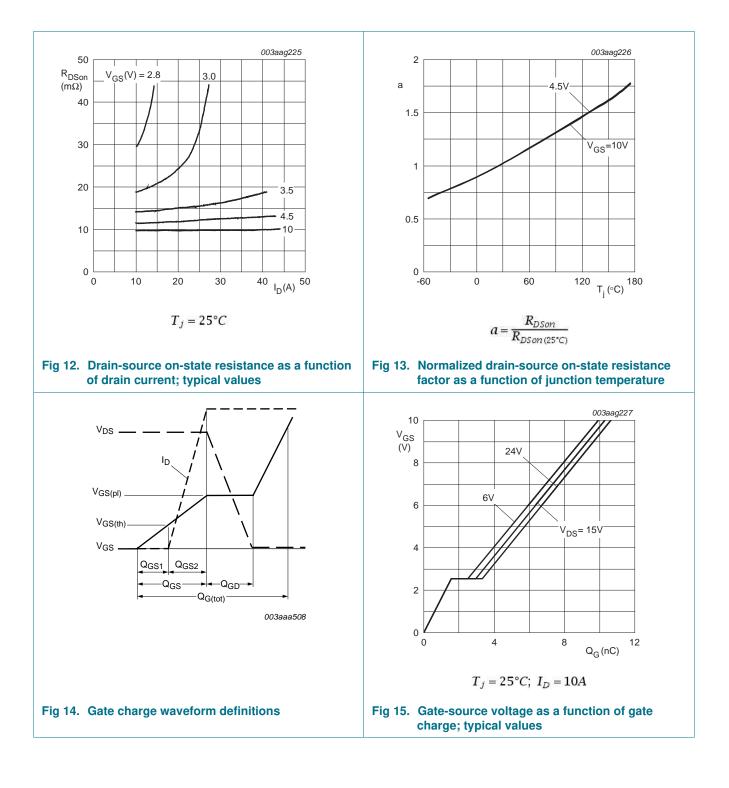
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	$V_{GS}$ = 0 V; $V_{DS}$ = 15 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	3.8	-	nC
Source-dra	in diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 10 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.85	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	17	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	7	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 V; I_S = 10 A;$	-	10	-	ns
t <sub>b</sub>	reverse recovery fall time	dl <sub>S</sub> /dt = -100 A/μs; V <sub>DS</sub> = 15 V; see <u>Figure 18</u>	-	7	-	ns



# PSMN011-30YLC

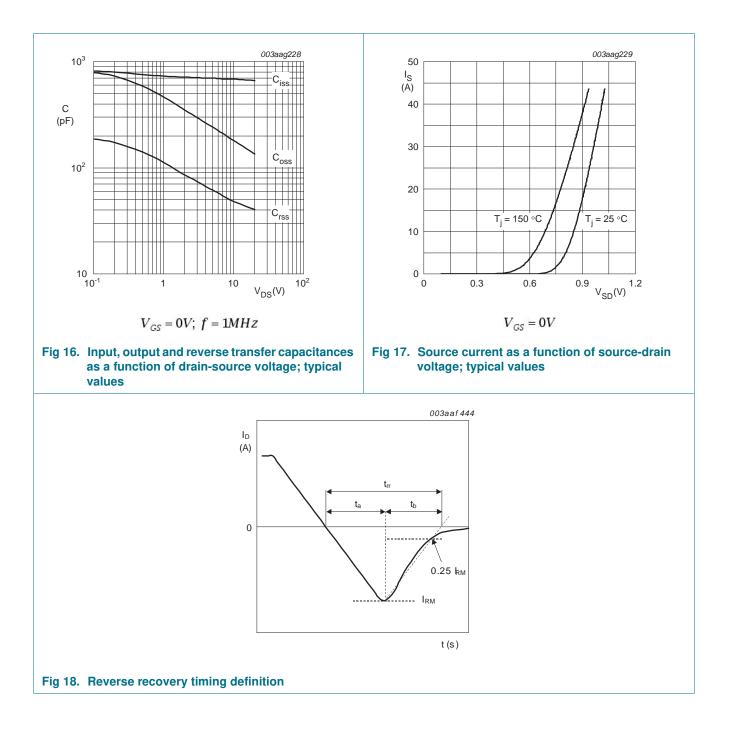


# PSMN011-30YLC



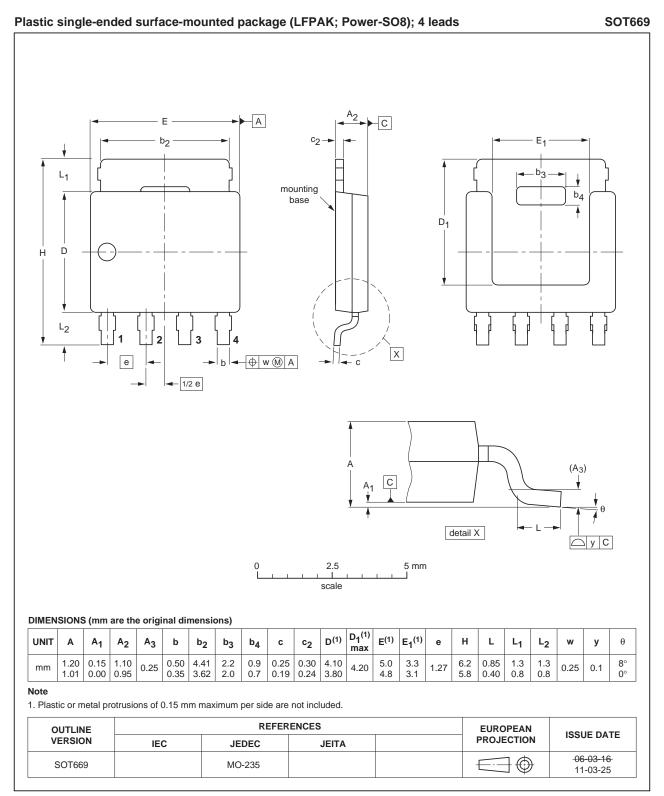
PSMN011-30YLC Product data sheet

# PSMN011-30YLC



#### N-channel 30 V 11.6 mΩ logic level MOSFET in LFPAK using NextPower technology

### 7. Package outline



#### Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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PSMN011-30YLC

N-channel 30 V 11.6 mΩ logic level MOSFET in LFPAK using NextPower technology

### 8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN011-30YLC v.3	20111024	Product data sheet	-	PSMN011-30YLC v.2
Modifications:	<ul> <li>Data sheet sta</li> </ul>	tus changed from prelimina	ry to product.	
	<ul> <li>Various change</li> </ul>	es to content.		
PSMN011-30YLC v.2	20110930	Preliminary data shee	·t -	PSMN011-30YLC v.1

N-channel 30 V 11.6 mΩ logic level MOSFET in LFPAK using NextPower technology

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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#### N-channel 30 V 11.6 mΩ logic level MOSFET in LFPAK using NextPower technology

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